

Electrical Characteristics $T_C=25\text{ }^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
On Characteristics						
V_{GS}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2	--	4	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\ \text{V}, I_D = 5\ \text{A}$	--	3.8	--	Ω
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\ \text{V}, I_D = 250\ \mu\text{A}$	500	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to $25\text{ }^\circ\text{C}$	--	0.7	--	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600\ \text{V}, V_{GS} = 0\ \text{V}$	--	--	1	μA
		$V_{DS} = 480\ \text{V}, T_C = 125\text{ }^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\ \text{V}, V_{DS} = 0\ \text{V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\ \text{V}, V_{DS} = 0\ \text{V}$	--	--	-100	nA
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 25\ \text{V}, V_{GS} = 0\ \text{V}, f = 1.0\ \text{MHz}$	--	1550	2020	pF
C_{oss}	Output Capacitance		--	164	212	pF
C_{rss}	Reverse Transfer Capacitance		--	17	24	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Time	$V_{DS} = 300\ \text{V}, I_D = 10\ \text{A}, R_G = 25\ \Omega$ (Note 4,5)	--	17	45	ns
t_r	Turn-On Rise Time		--	65	145	ns
$t_{d(off)}$	Turn-Off Delay Time		--	141	270	ns
t_f	Turn-Off Fall Time		--	75	160	ns
Q_g	Total Gate Charge	$V_{DS} = 480\ \text{V}, I_D = 10\ \text{A}, V_{GS} = 10\ \text{V}$ (Note 4,5)	--	43	55	nC
Q_{gs}	Gate-Source Charge		--	6.4	--	nC
Q_{gd}	Gate-Drain Charge		--	18	--	nC
Source-Drain Diode Maximum Ratings and Characteristics						
I_S	Continuous Source-Drain Diode Forward Current		--	--	10	A
I_{SM}	Maximum Pulsed Source-Drain Diode Forward Current		--	--	40	
V_{SD}	Source-Drain Diode Forward Voltage	$I_S = 10\ \text{A}, V_{GS} = 0\ \text{V}$	--	--	1.4	V
t_{rr}	Reverse Recovery Time	$I_S = 10\ \text{A}, V_{GS} = 0\ \text{V}, di_f/dt = 100\ \text{A}/\mu\text{s}$ (Note 4)	--	425	--	ns
Q_{rr}	Reverse Recovery Charge		--	4.4	--	μC

Notes ;

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L=14.2\ \text{mH}, V_{DD}=50\ \text{V}, R_G=25\ \Omega$, Starting $T_J=25\text{ }^\circ\text{C}$
3. $I_{SD} \leq 10\ \text{A}, di/dt \leq 200\ \text{A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J=25\text{ }^\circ\text{C}$
4. Pulse Test : Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$
5. Essentially Independent of Operating Temperature

Typical Characteristics

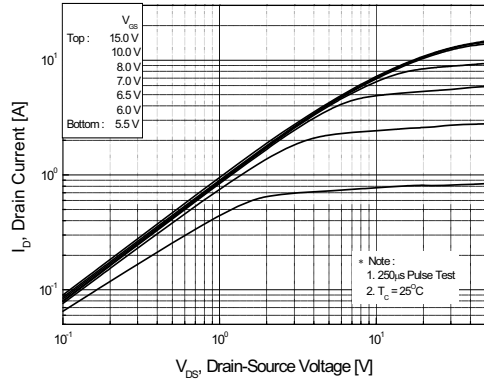


Figure 1. On Region Characteristics

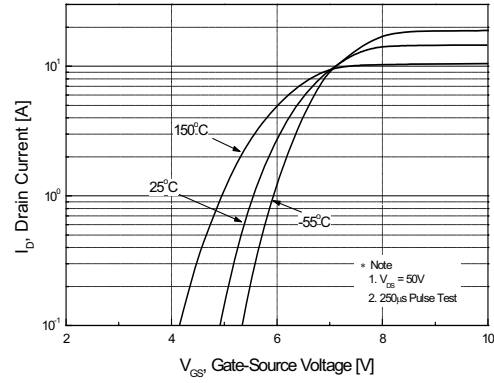


Figure 2. Transfer Characteristics

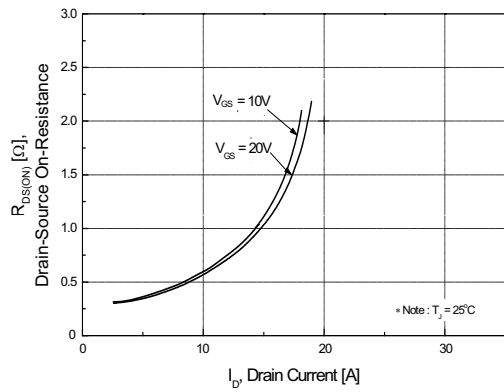


Figure 3. On Resistance Variation vs Drain Current and Gate Voltage

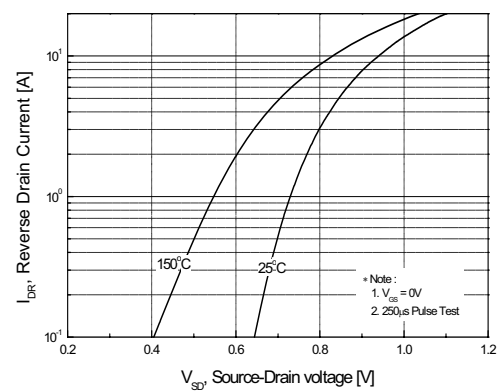


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

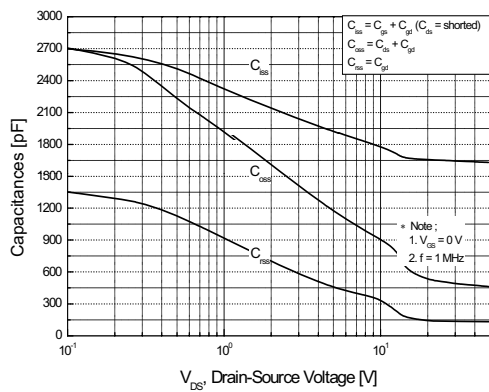


Figure 5. Capacitance Characteristics

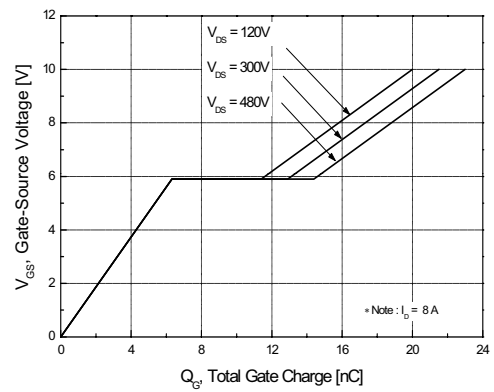


Figure 6. Gate Charge Characteristics

Typical Characteristics (continued)

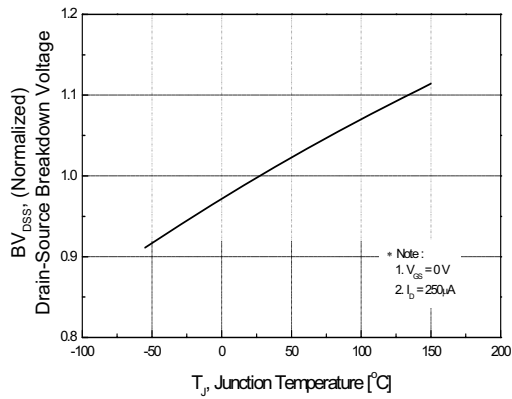


Figure 7. Breakdown Voltage Variation vs Temperature

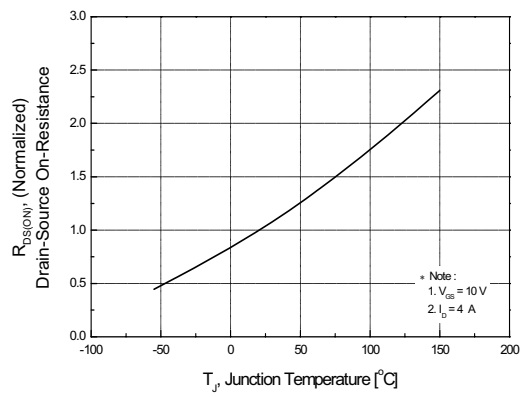


Figure 8. On-Resistance Variation vs Temperature

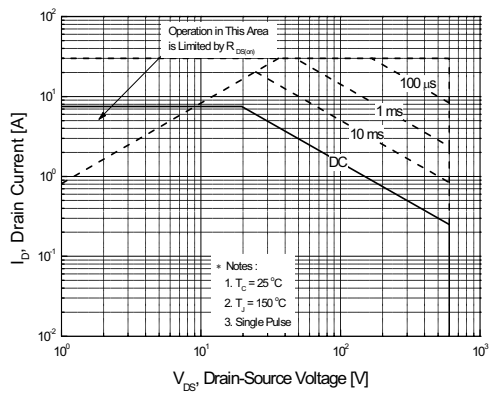


Figure 9. Maximum Safe Operating Area

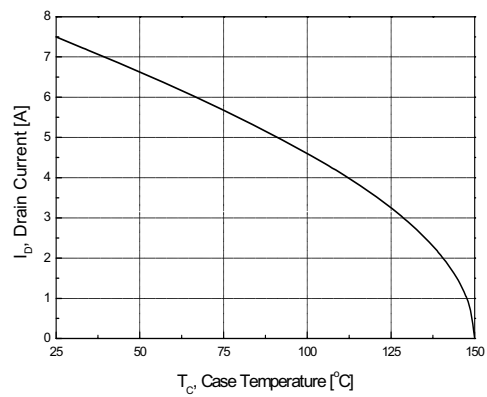


Figure 10. Maximum Drain Current vs Case Temperature

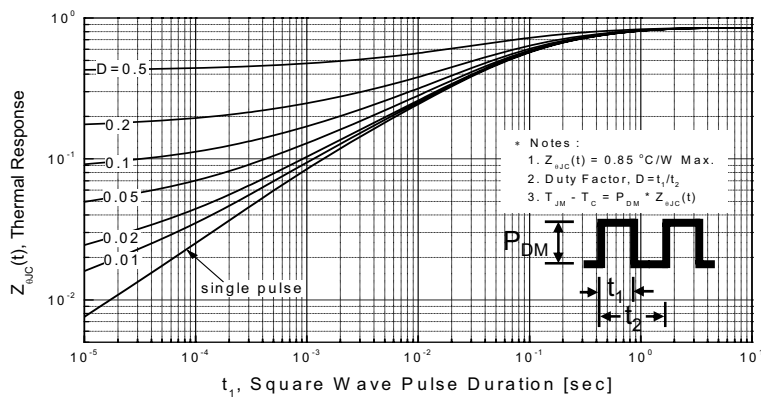


Figure 11. Transient Thermal Response Curve

Fig 12. Gate Charge Test Circuit & Waveform

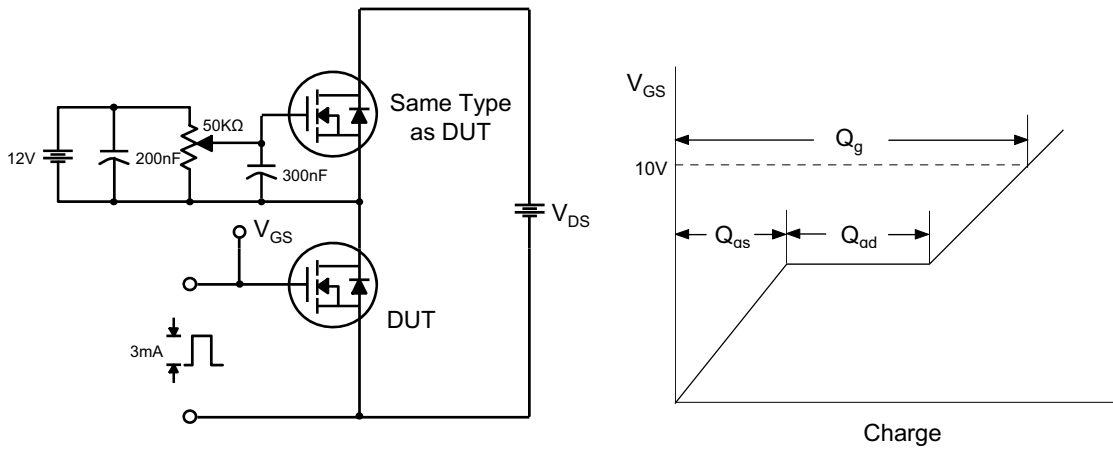


Fig 13. Resistive Switching Test Circuit & Waveforms

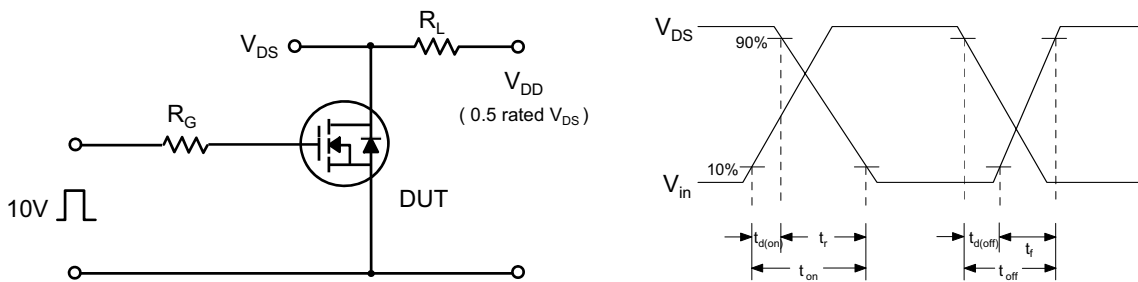


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

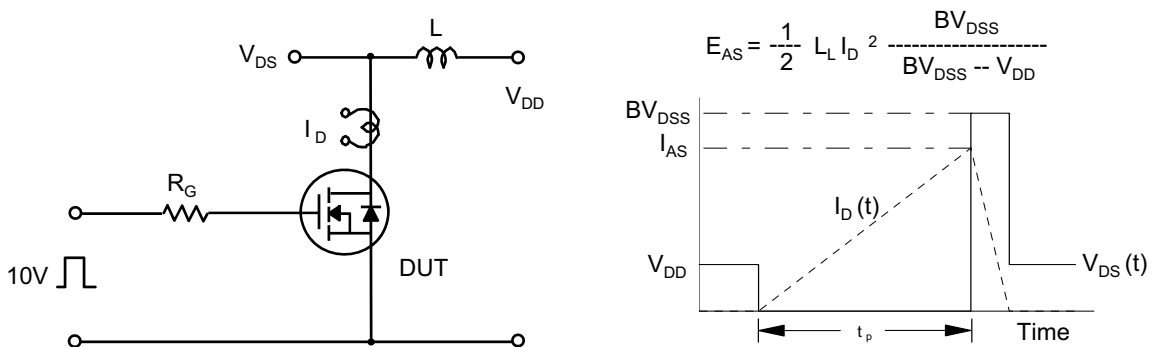


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

